

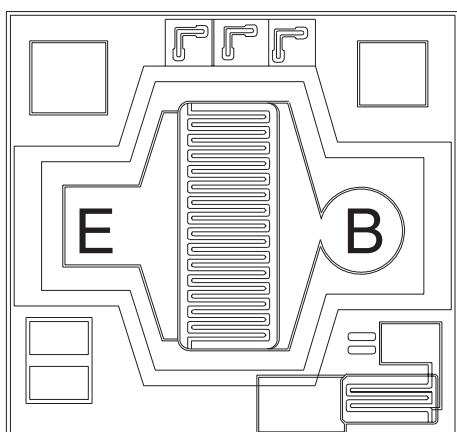
PROCESS CP618
Small Signal Transistor
PNP - Silicon RF Transistor Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	21.7 x 21.7 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	3.5 MILS DIAMETER
Emitter Bonding Pad Area	3.5 x 3.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 10,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

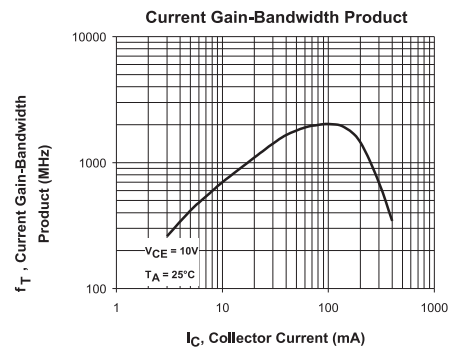
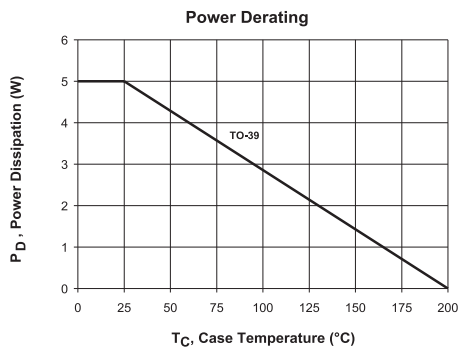
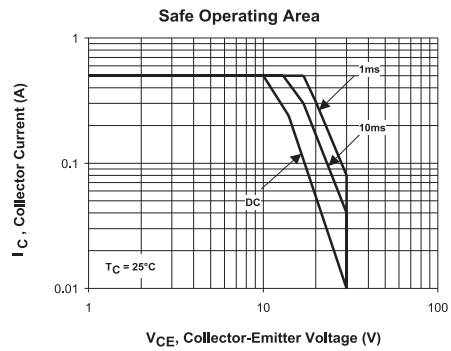
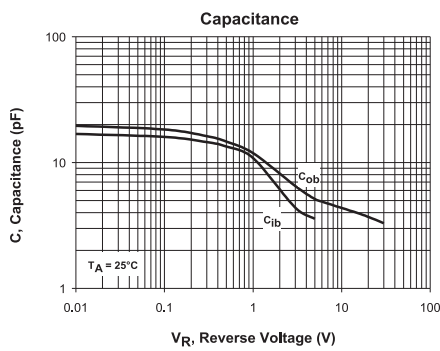
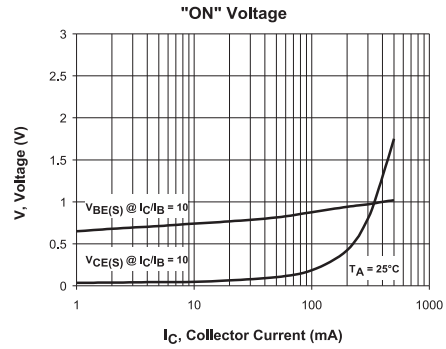
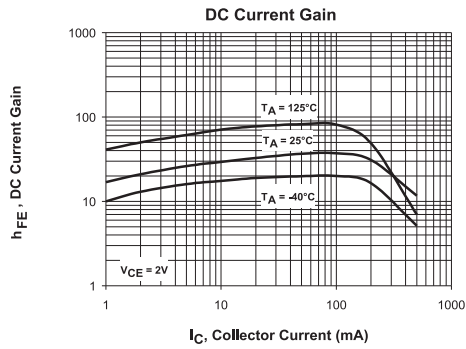
23,990

PRINCIPAL DEVICE TYPES

CM5583

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R2 (1-August 2002)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R2 (1-August 2002)